

LH52256C/CH

CMOS 256K (32K × 8) Static RAM

FEATURES

- 32,768 × 8 bit organization
- Access time: 70 ns (MAX.)
- Supply current:
 - Operating: 45 mA (MAX.)
 - 10 mA (MAX.) (t_{RC} , $t_{WC} = 1 \mu s$)
 - Standby: 40 μA (MAX.)
- Data retention current: 1.0 μA (MAX.)
 - ($V_{CCDR} = 3 V$, $T_A = 25^\circ C$)
- Wide operating voltage range:
 - 4.5 V \pm 5.5 V
- Operating temperature:
 - Commerical temperature 0°C to +70°C
 - Industrial temperature -40° to +85°C
- Fully-static operation
- Three-state outputs
- Not designed or rated as radiation hardened
- Package:
 - 28-pin, 600-mil DIP
 - 28-pin, 450-mil SOP
 - 28-pin, 300-mil SK-DIP
 - 28-pin, 8 × 3 mm² TSOP (Type I)
- N-type bulk silicon

DESCRIPTION

The LH52256C is a Static RAM organized as 32,768 × 8 bits which provides low-power standby mode. It is fabricated using silicon-gate CMOS process technology.

PIN CONNECTIONS

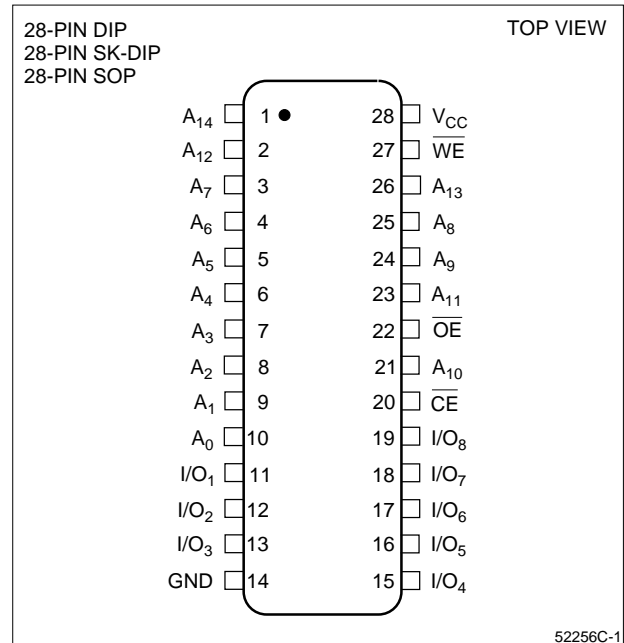


Figure 1. Pin Connections

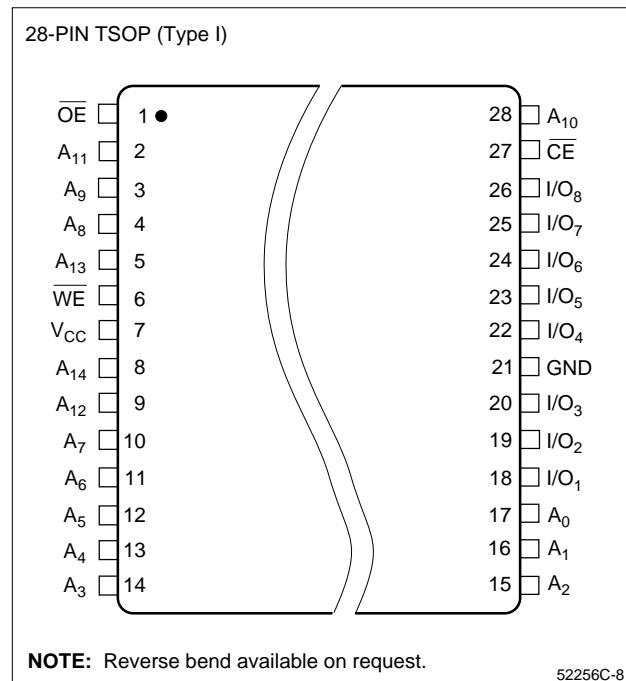


Figure 2. TSOP (Type I) Pin Connections

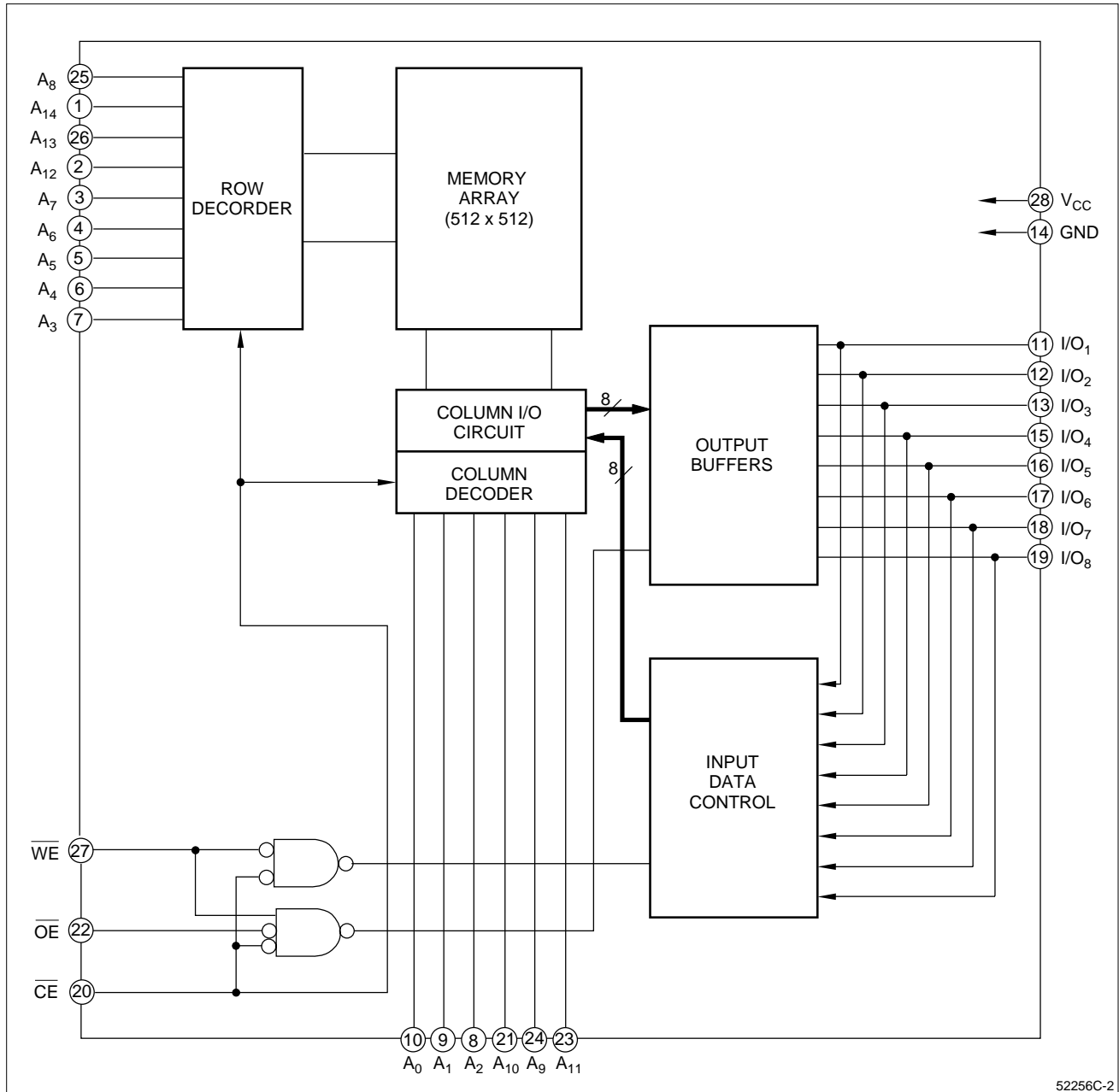


Figure 3. LH52256C Block Diagram

PIN DESCRIPTION

SIGNAL	PIN NAME
A ₀ - A ₁₄	Address inputs
CE	Chip enable
WE	Write enable
OE	Output enable

SIGNAL	PIN NAME
I/O ₁ - I/O ₈	Data inputs and outputs
V _{CC}	Power supply
GND	Ground

TRUTH TABLE

\overline{CE}	\overline{WE}	\overline{OE}	MODE	I/O ₁ - I/O ₈	SUPPLY CURRENT	NOTE
H	X	X	Standby	High impedance	Standby (I _{SB})	1
L	H	L	Read	Data output	Active (I _{CC})	1
L	H	H	Output disable	High impedance	Active (I _{CC})	1
L	L	X	Write	Data input	Active (I _{CC})	1

NOTE:

1. X = Don't care, L = Low, H = High

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT	NOTE
Supply voltage	V _{CC}	-0.5 to +7.0	V	1
Input voltage	V _{IN}	-0.5 to V _{CC} + 0.5	V	1, 2
Operating temperature	T _{OPR}	0 to +70	°C	—
Storage temperature	T _{STG}	-65 to +150	°C	—

NOTES:

1. The maximum applicable voltage on any pin with respect to GND.
2. Undershoot of -3.0 V is allowed width of pulse below 50 ns.

RECOMMENDED DC OPERATING CONDITIONS (T_A = 0°C to +70°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	NOTE
Supply voltage	V _{CC}	4.5	5.0	5.5	V	—
Input voltage	V _{IH}	2.2	—	V _{CC} + 0.5	V	—
	V _{IL}	-0.5	—	0.8	V	1

NOTE:

1. Undershoot of -3.0 V is allowed width of pulse below 50 ns.

DC ELECTRICAL CHARACTERISTICS (T_A = 0°C to +70°C, V_{CC} = 4.5 V to 5.5 V)

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Input leakage current	I _{LI}	V _{IN} = 0 V to V _{CC}	-1.0	—	1.0	μA
Output leakage current	I _{LO}	CE = V _{IH} or OE = V _{IH} V _{IO} = 0 V to V _{CC}	-1.0	—	1.0	μA
Operating supply current	I _{CC}	Minimum cycle, V _{IN} = V _{IL} or V _{IH} I _{IO} = 0 mA, CE = V _{IL}	—	25	45.0	mA
	I _{CC1}	t _{RC} , t _{WC} = 1 μs, V _{IN} = V _{IL} or V _{IH} , I _{IO} = 0 mA, CE = V _{IL}	—	—	10.0	
Standby current	I _{SB}	CE ≥ V _{CC} - 0.2 V	—	0.6	40.0	μA
	I _{SB1}	CE = V _{IH}	—	—	3.0	mA
Output voltage	V _{OL}	I _{OL} = 2.1 mA	—	—	0.4	V
	V _{OH}	I _{OH} = -1.0 mA	2.4	—	—	

NOTE:

Typical values at V_{CC} = 5.0 V, T_A = 25°C

**AC ELECTRICAL CHARACTERISTICS
AC Test Conditions**

PARAMETER	MODE	NOTE
Input pulse level	0.6 V to 2.4 V	—
Input rise and fall time	10 ns	—
Input and output timing Ref. level	1.5 V	—
Output load	1 TTL + C _L (100 pF)	1

NOTE:

1. Including scope and jig capacitance.

READ CYCLE (T_A = 0°C to +70°C, V_{CC} = 4.5 V to 5.5 V)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	NOTE
Read cycle time	t _{RC}	70	—	ns	—
Address access time	t _{AA}	—	70	ns	—
CE access time	t _{ACE}	—	70	ns	—
Output enable to output valid	t _{OE}	—	35	ns	—
Output hold from address change	t _{OH}	10	—	ns	—
CE Low to output active	t _{LZ}	10	—	ns	1
OE Low to output active	t _{OLZ}	5	—	ns	1
CE High to output in High impedance	t _{HZ}	0	30	ns	1
OE High to output in High impedance	t _{OHZ}	0	30	ns	1

NOTES:

1. Active output to high-impedance and high-impedance to output active tests specified for a ±200 mV transition from steady state levels into the test load.

WRITE CYCLE ($T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$, $V_{CC} = 4.5\text{ V}$ to 5.5 V)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	NOTE
Write cycle time	t_{WC}	70	—	ns	—
CE Low to end of write	t_{CW}	45	—	ns	—
Address valid to end of write	t_{AW}	45	—	ns	—
Address setup time	t_{AS}	0	—	ns	—
Write pulse width	t_{WP}	35	—	ns	—
Write recovery time	t_{WR}	0	—	ns	—
Input data setup time	t_{DW}	30	—	ns	—
Input data hold time	t_{DH}	0	—	ns	—
\overline{WE} High to output active	t_{OW}	5	—	ns	1
\overline{WE} Low to output in High impedance	t_{WZ}	0	30	ns	1
\overline{OE} High to output in High impedance	t_{OHZ}	0	30	ns	1

NOTE:

- Active output to high-impedance and high-impedance to output active tests specified for a $\pm 200\text{ mV}$ transition from steady state levels into the test load.

CAPACITANCE ($T_A = 25^\circ\text{C}$, $f = 1\text{ MHz}$)

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT	NOTE
Input capacitance	C_{IN}	$V_{IN} = 0\text{ V}$	—	—	7	pF	1
I/O capacitance	$C_{I/O}$	$V_{I/O} = 0\text{ V}$	—	—	10	pF	1

NOTE:

- This parameter is sampled and not production tested.

DATA RETENTION CHARACTERISTICS ($T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$)

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT	NOTE	
Data retention supply voltage	V_{CCDR}	$\overline{CE} \geq V_{CCDR} - 0.2\text{ V}$	2.0	—	5.5	V	—	
Data retention supply current	I_{CCDR}	$V_{CCDR} = 3.0\text{ V}$	$T_A = 25^\circ\text{C}$	—	0.3	1.0	μA	—
			$T_A = 40^\circ\text{C}$	—	—	3.0		—
		$\overline{CE} \geq V_{CCDR} - 0.2\text{ V}$					15	
Chip enable setup time	t_{CDR}	—	0	—	—	ns	—	
Chip enable hold time	t_R	—	t_{RC}	—	—	ns	1	

NOTE:

- t_{RC} = Read cycle time.
- Typical values at $T_A = 25^\circ\text{C}$

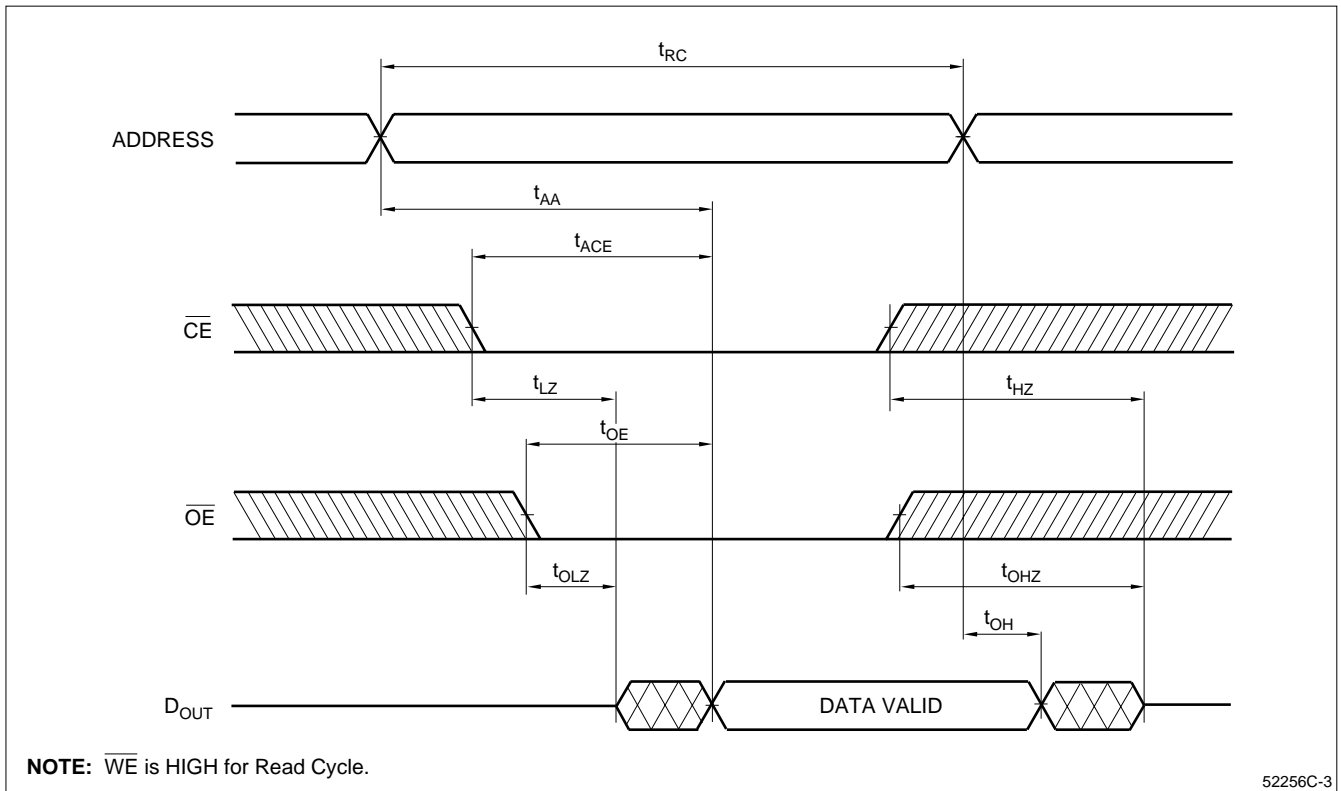
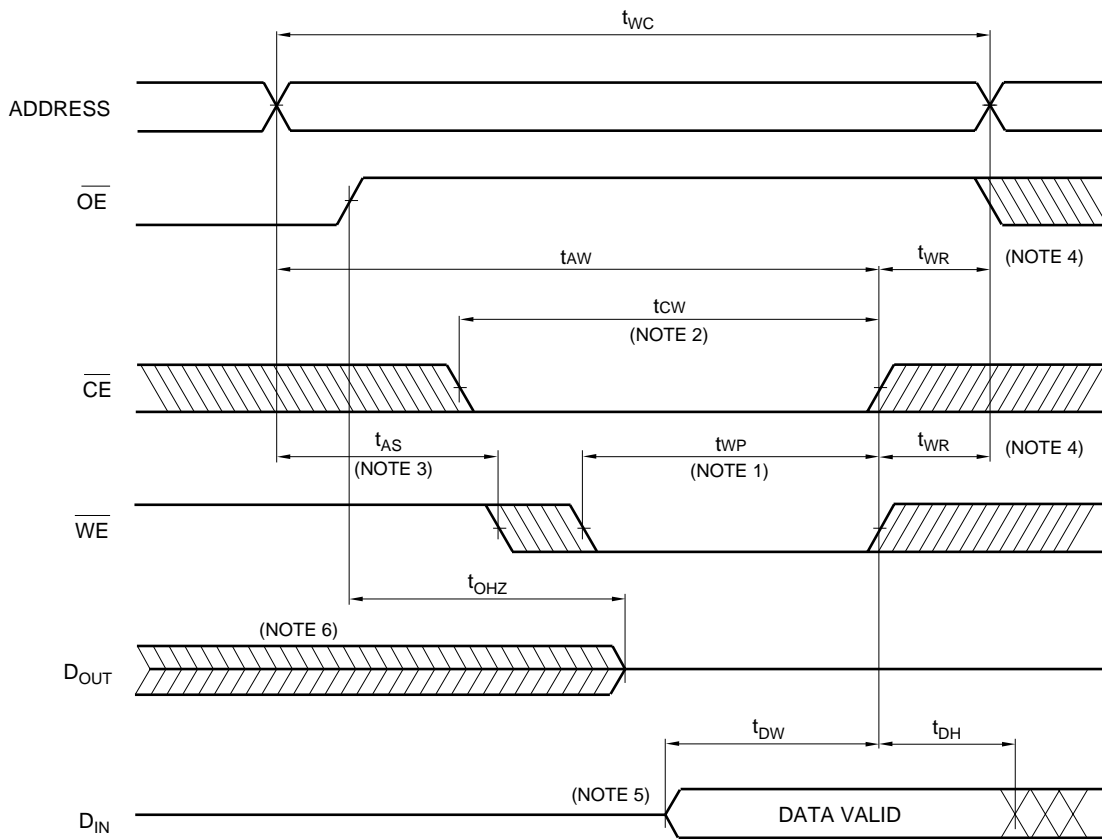


Figure 4. Read Cycle

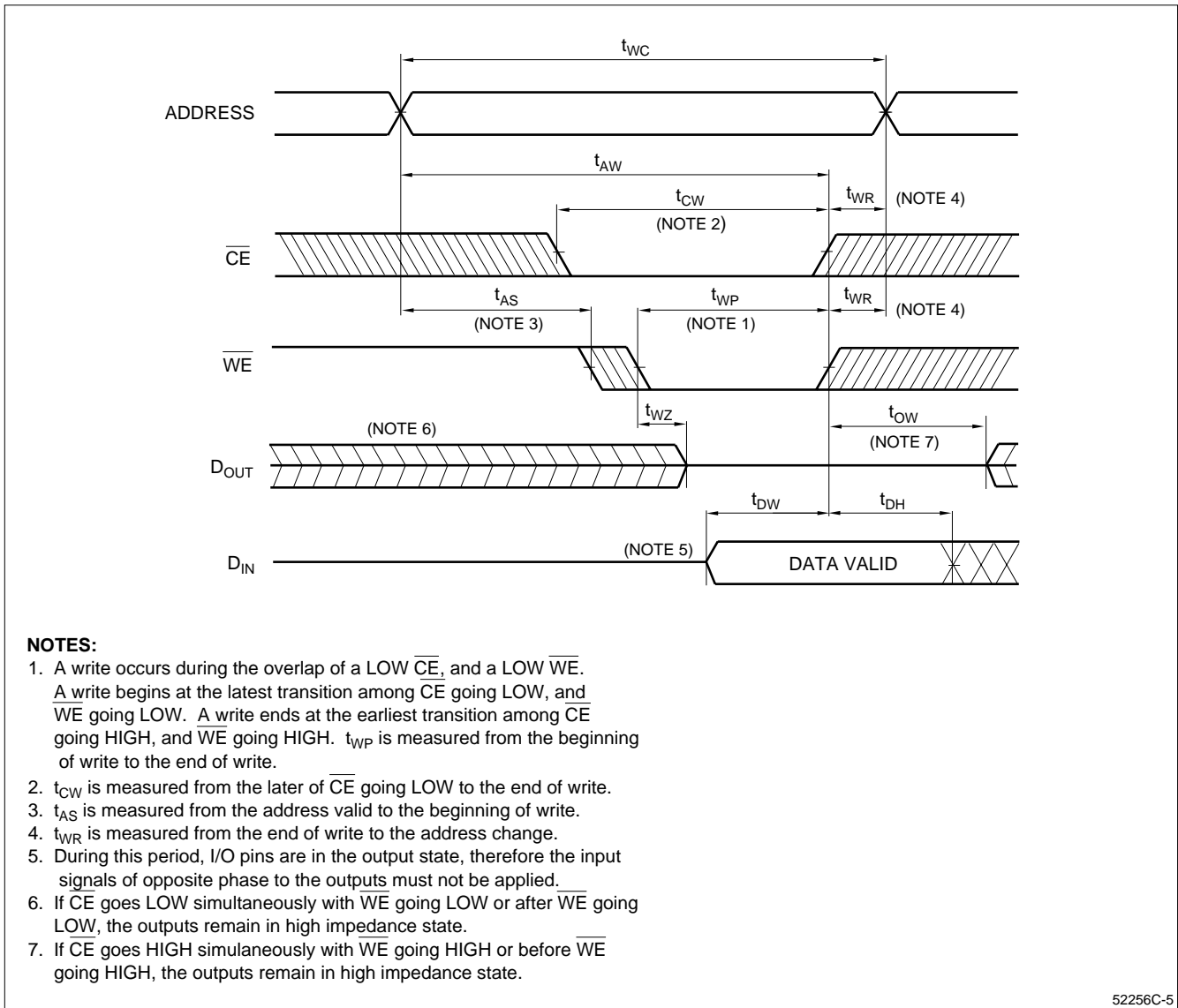


NOTES:

1. A write occurs during the overlap of a LOW \overline{CE} , and a LOW \overline{WE} .
A write begins at the latest transition among \overline{CE} going LOW, and \overline{WE} going LOW. A write ends at the earliest transition among \overline{CE} going HIGH, and \overline{WE} going HIGH. t_{WP} is measured from the beginning of write to the end of write.
2. t_{CW} is measured from the later of \overline{CE} going LOW to the end of write.
3. t_{AS} is measured from the address valid to the beginning of write.
4. t_{WR} is measured from the end of write to the address change.
5. During this period, I/O pins are in the output state, therefore the input signals of opposite phase to the outputs must not be applied.
6. If \overline{CE} goes LOW simultaneously with \overline{WE} going LOW or after \overline{WE} going LOW, the outputs remain in high impedance state.
7. If \overline{CE} goes HIGH simultaneously with \overline{WE} going HIGH or before \overline{WE} going HIGH, the outputs remain in high impedance state.

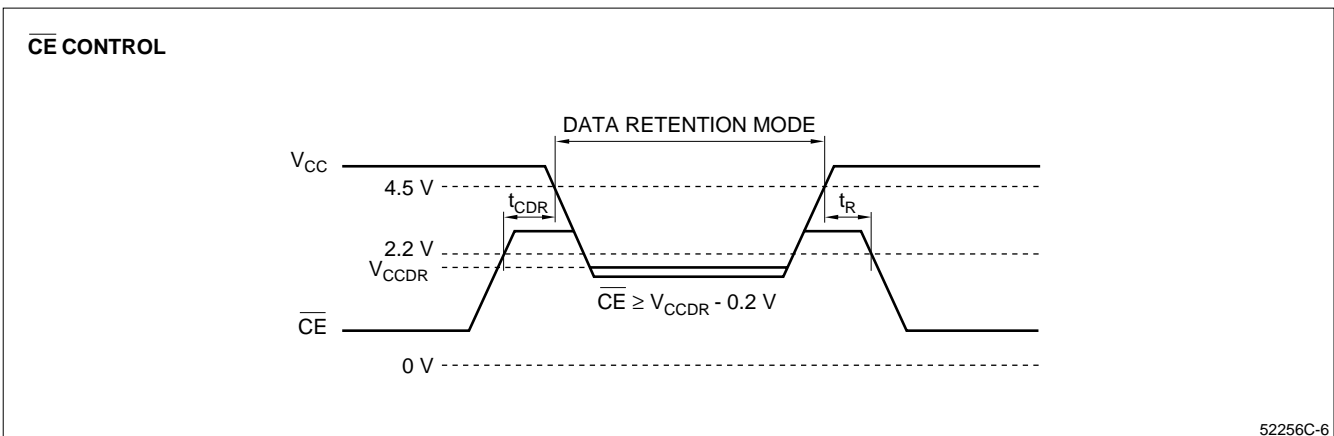
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Figure 5. Write Cycle (OE Controlled)

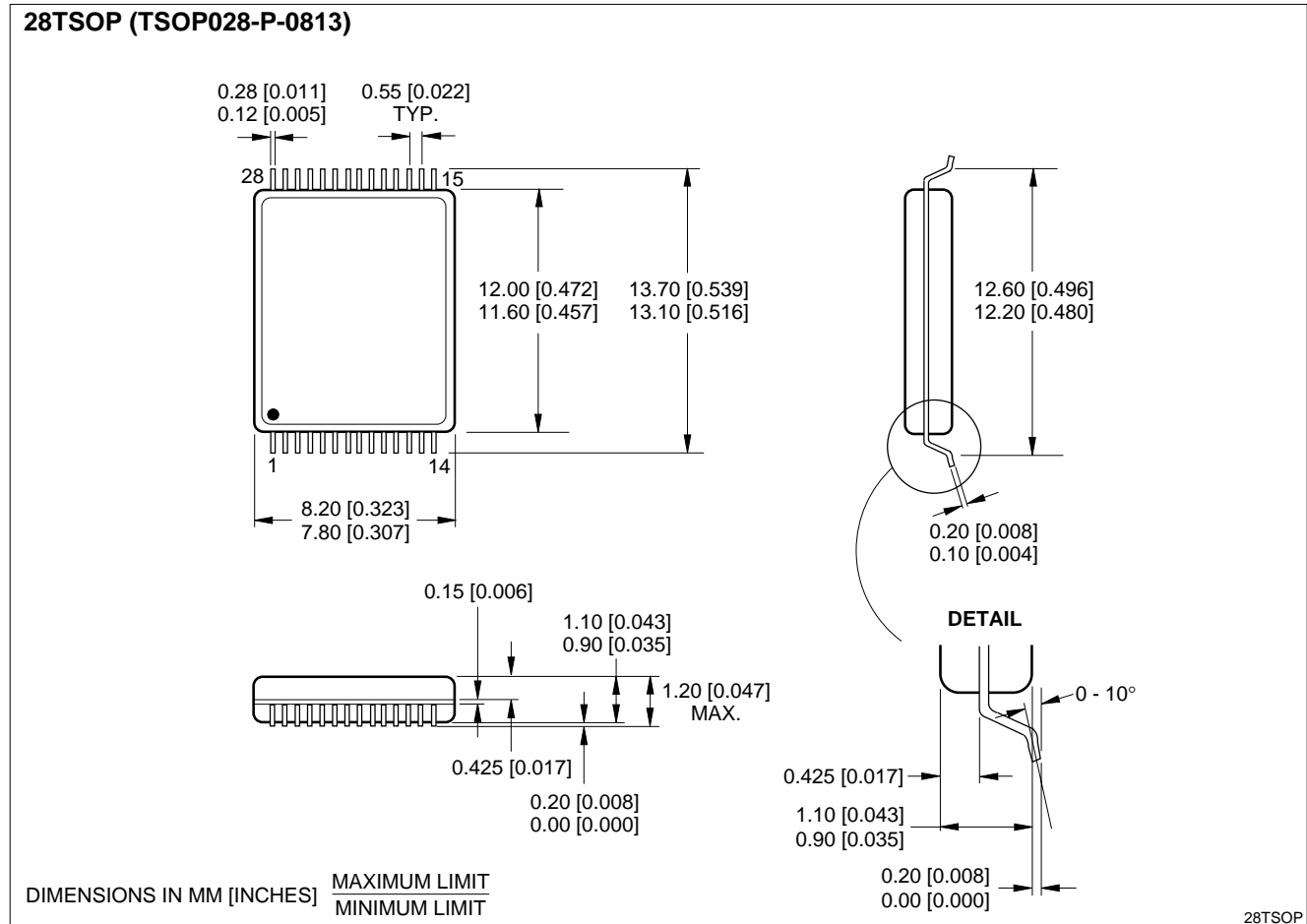
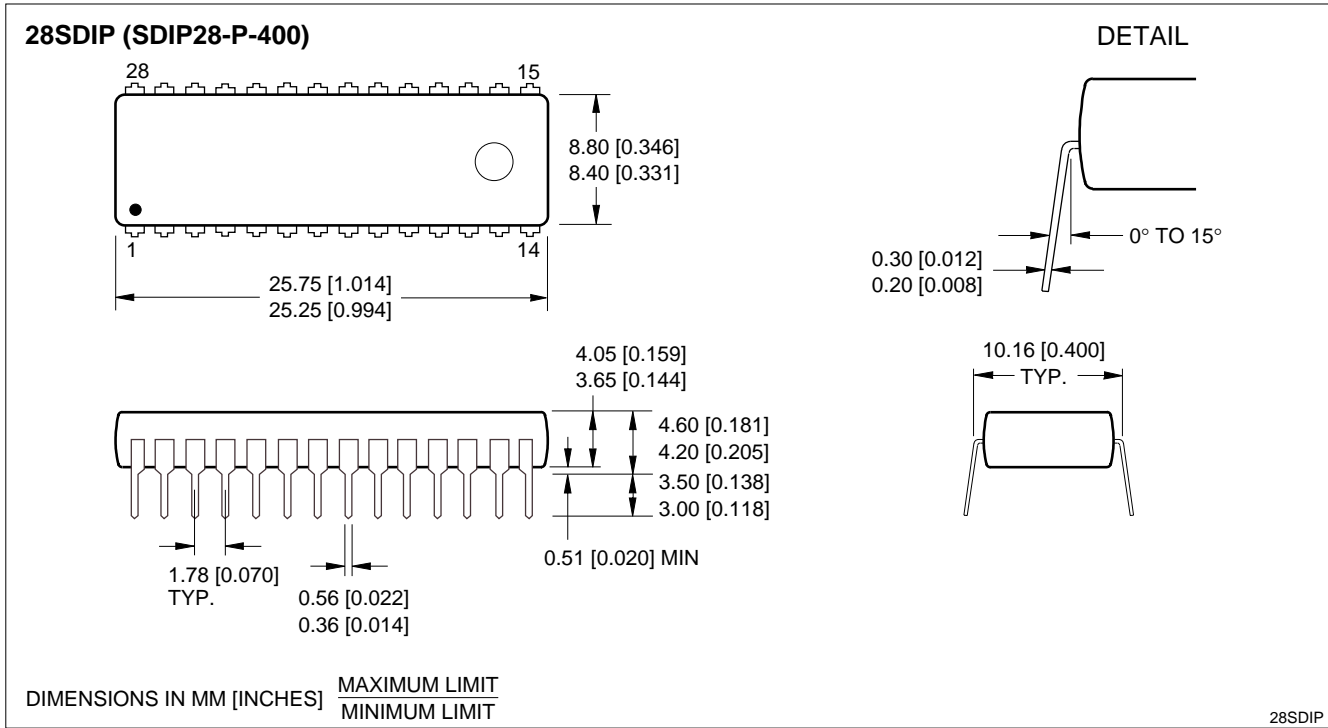


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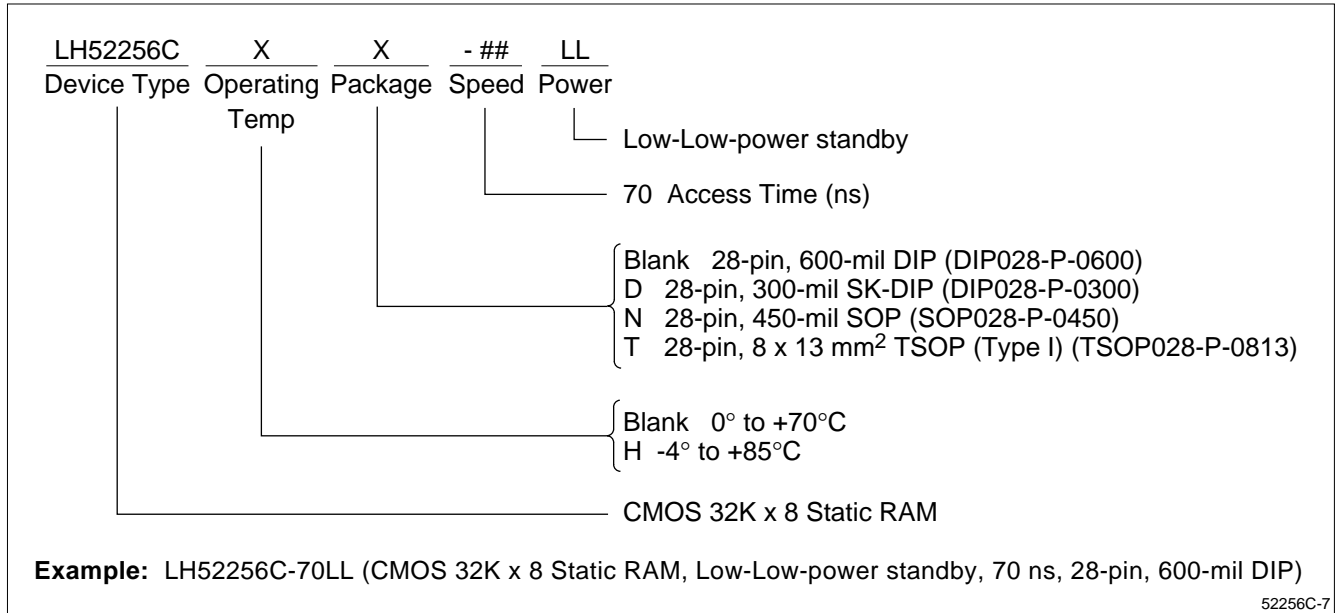
Figure 6. Write Cycle (\overline{OE} Low Fixed)



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